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NTE2677

Silicon NPN Transistor

High Voltage, High Speed Switch

TO3P(H)IS Type Package

Features:

- High Breakdown Voltage: $V_{CBO} = 1500V$ Min
- High Switching Speed
- Low Saturation Voltage

Applications:

- Color TV Horizontal Deflection Output

Absolute Maximum Ratings: ($T_A = +25^\circ C$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	1500V
Collector–Emitter Voltage, V_{CEO}	800V
Emitter–Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	10A
Pulse	30A
Continuous Base Current, I_B	5A
Collector Power Dissipation ($T_C = +25^\circ C$), P_C	70W
Operating Junction Temperature, T_J	$+150^\circ C$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ C$

Electrical Characteristics: ($T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 8A, I_B = 1.6A$	–	–	5.0	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 8A, I_B = 1.6A$	–	–	1.5	V
Collector Cutoff Current	I_{CES}	$V_{CE} = 1400V, V_{BE} = 0$	–	–	1.0	mA
	I_{CBO}	$V_{CB} = 800V, I_E = 0$	–	–	10	μA
		$V_{EB} = 4V, I_C = 0$	–	–	1.0	mA
DC Current Gain	h_{FE}	$I_C = 1A, V_{CE} = 5V$	15	–	40	
		$I_C = 8A, V_{CE} = 5V$	8	–	10	
Fall Time	t_f	$I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A,$ $V_{CC} = 200V, R_L = 33.3\Omega$	–	–	0.3	μs

